ABSTRACT OF THE DISCLOSURE

The invention relates to a . Method of forming a structure (30) comprising a layer (1', 2) that is taken-off from a donor wafer (10), the donor wafer comprising prior to taking-off a first layer (1) made of a semi conductor material comprising germanium, the method comprising the following steps:

(a) formation of a weakness zone (4) in the thickness of said first layer (1) comprising germanium bonding the donor wafer to a host wafer;

(b) bonding the donor wafer to a host wafer;

(c) supplying energy so as to weaken the donor wafer (10) at the level of the weakness zone (4);

wherein step (a) is carried out by subjecting the donor wafer to a co-implantation of at least two different atomic species, and step (c) is carried out by performing a thermal treatment at a temperature between 300°C and 400°C, for a duration that can last up from 30 minutes to four hours.

Figure 3d